

# High Efficiency Thyristor

$$V_{RRM} = 1200 \text{ V}$$

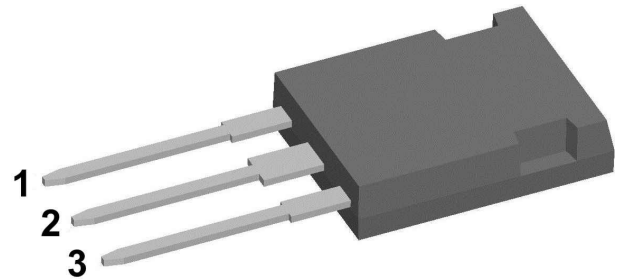
$$I_{TAV} = 80 \text{ A}$$

$$V_T = 1.38 \text{ V}$$

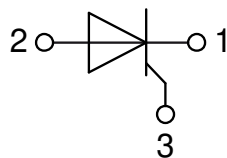
## Single Thyristor

Part number

**CLA80E1200HF**



Backside: anode



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: PLUS247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

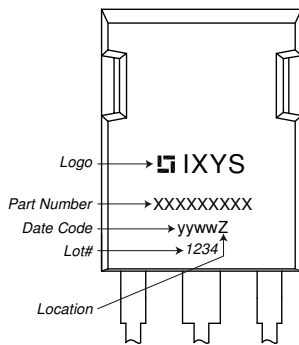


Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		50	$\mu A$
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		5	mA
$V_T$	forward voltage drop	$I_T = 80 A$	$T_{VJ} = 25^{\circ}C$		1.40	V
		$I_T = 160 A$			1.77	V
		$I_T = 80 A$	$T_{VJ} = 125^{\circ}C$		1.38	V
		$I_T = 160 A$			1.87	V
$I_{TAV}$	average forward current	$T_C = 115^{\circ}C$	$T_{VJ} = 150^{\circ}C$		80	A
$I_{T(RMS)}$	RMS forward current	180° sine			126	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.88	V
$r_T$	slope resistance				6.3	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				0.2	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.3		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		620	W
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		900	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		970	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		765	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		825	A
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		4.05	kA <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		3.92	kA <sup>2</sup> s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		2.93	kA <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		2.83	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		36	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
$P_{GAV}$	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 240 A$			150	A/ $\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.3 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 80 A$			500	A/ $\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 150^{\circ}C$		1000	V/ $\mu s$
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.5	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		38	mA
			$T_{VJ} = -40^{\circ}C$		80	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V
$I_{GD}$	gate non-trigger current				5	mA
$I_L$	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		150	mA
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$				
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu s$
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V; I_T = 80 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 20 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	$\mu s$



Package PLUS247		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				6		g
$F_C$	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	5.5			mm
$d_{Spb/Apb}$		terminal to backside	5.5			mm

**Product Marking**



**Part description**

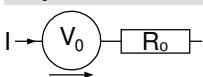
- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 80 = Current Rating [A]
- E = Single Thyristor
- 1200 = Reverse Voltage [V]
- HF = PLUS247 (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA80E1200HF	CLA80E1200HF	Tube	30	508680

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 150^{\circ}C$

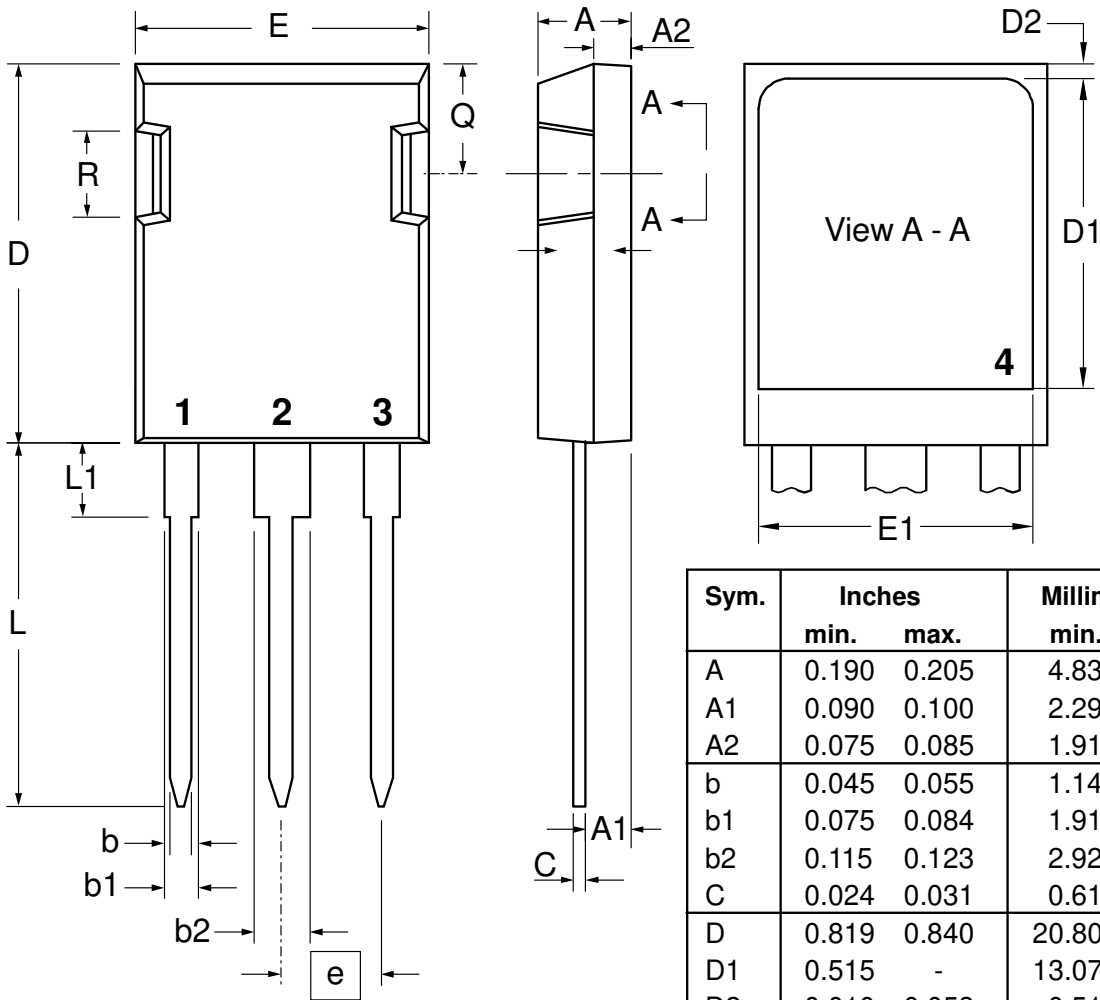


**Thyristor**

$V_{0\ max}$	threshold voltage	0.88	V
$R_{0\ max}$	slope resistance *	3.8	mΩ



**Outlines PLUS247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.190	0.205	4.83	5.21
A1	0.090	0.100	2.29	2.54
A2	0.075	0.085	1.91	2.16
b	0.045	0.055	1.14	1.40
b1	0.075	0.084	1.91	2.13
b2	0.115	0.123	2.92	3.12
C	0.024	0.031	0.61	0.80
D	0.819	0.840	20.80	21.34
D1	0.515	-	13.07	-
D2	0.010	0.053	0.51	1.35
E	0.620	0.635	15.75	16.13
E1	0.530	-	13.45	-
e	0.215 BSC		5.45 BSC	
L	0.780	0.800	19.81	20.32
L1	0.150	0.170	3.81	4.32
Q	0.220	0.244	5.59	6.20
R	0.170	0.190	4.32	4.83



## Thyristor

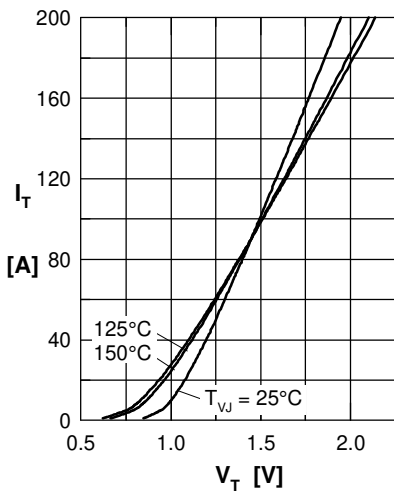


Fig. 1 Forward characteristics

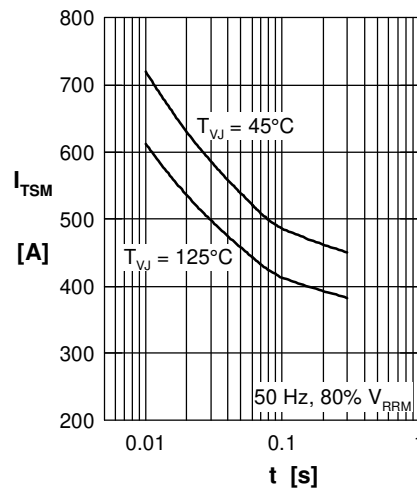


Fig. 2 Surge overload current

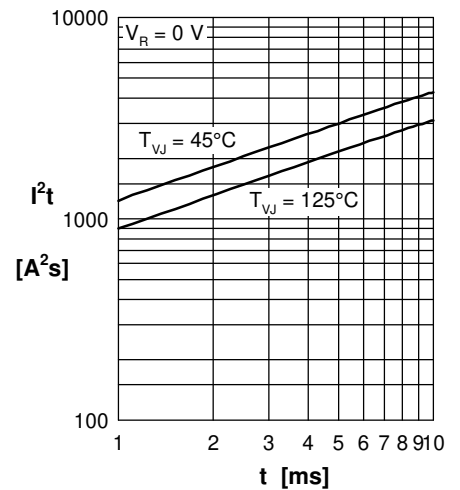


Fig. 3  $I^2t$  versus time (1-10 ms)

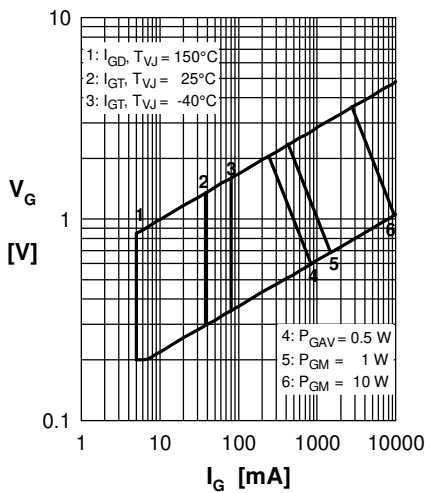


Fig. 4 Gate trigger characteristics

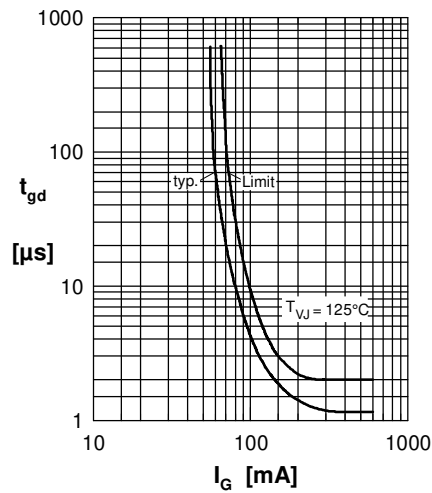


Fig. 5 Gate controlled delay time

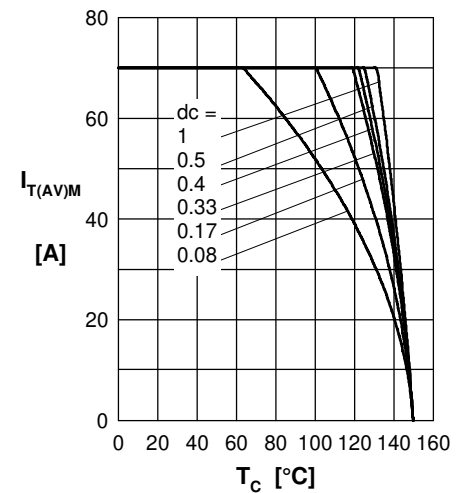


Fig. 6 Max. forward current at case temperature

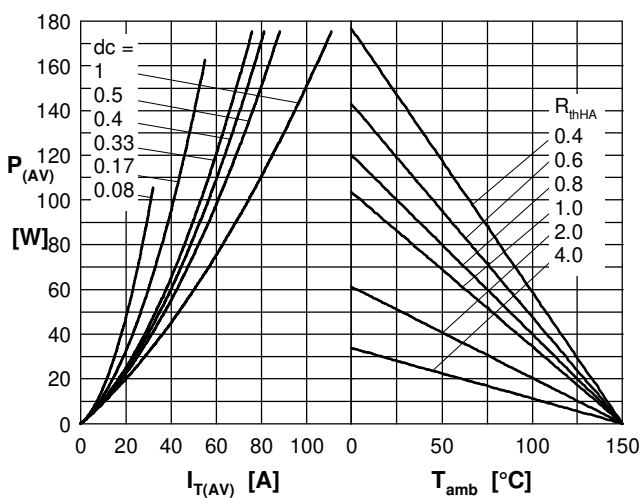


Fig. 7a Power dissipation versus direct output current  
Fig. 7b and ambient temperature

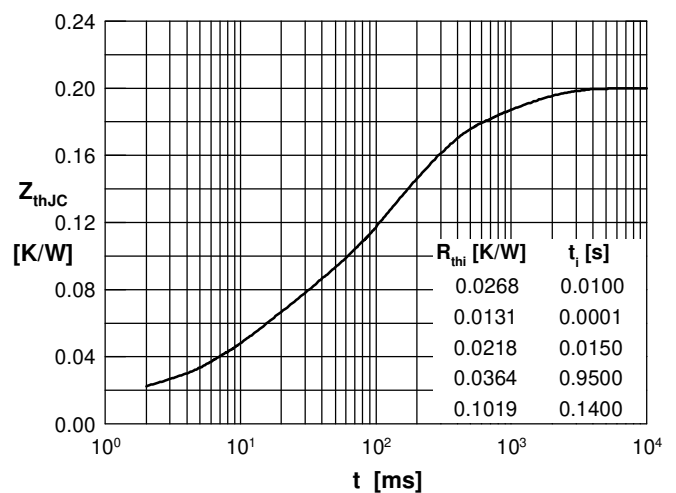


Fig. 8 Transient thermal impedance